SEMICONDUCTOR DEVICE HAVING A STRAINED REGION

ABSTRACT

The present disclosure provides devices and methods which provide for strained epitaxial regions. A method of semiconductor fabrication is provided that includes forming a gate structure over a fin of a semiconductor substrate and forming a recess in the fin adjacent the gate structure. A sidewall of the recess is then altered. Exemplary alterations include having an altered profile, treating the sidewall, and forming a layer on the sidewall. An epitaxial region is then grown in the recess. The epitaxial region interfaces the altered sidewall of the recess and is a strained epitaxial region.

Figure 2